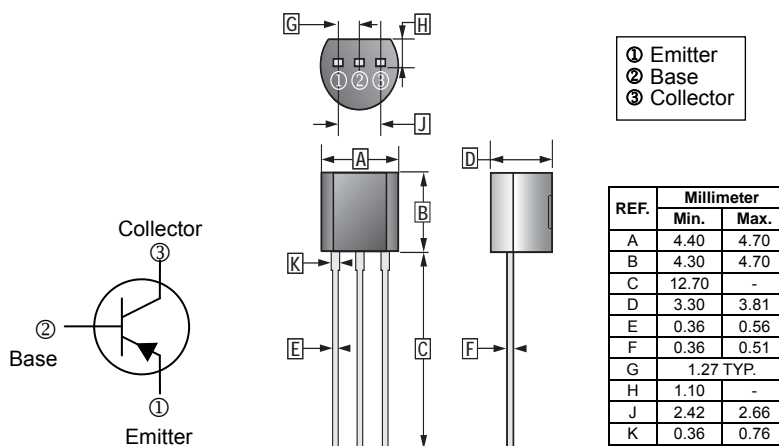


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- PNP Silicon Epitaxial Transistor for Switching and Amplifier Applications.
- Complementary of the 2N4124

TO-92



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	-25	V
Collector to Emitter Voltage	V_{CE0}	-25	V
Emitter to Base Voltage	V_{EB0}	-4	V
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	625	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C} / \text{W}$
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to Base Breakdown Voltage	$V_{(BR)CB0}$	-25	-	-	V	$I_C = -0.01\text{mA}, I_E = 0\text{A}$
Collector to Emitter Breakdown Voltage	$V_{(BR)CE0}$	-25	-	-	V	$I_C = -1\text{mA}, I_B = 0\text{A}$
Emitter to Base Breakdown Voltage	$V_{(BR)EB0}$	-4	-	-	V	$I_E = -0.01\text{mA}, I_C = 0\text{A}$
Collector Cut-Off Current	I_{CB0}	-	-	-50	nA	$V_{CB} = -20\text{V}, I_E = 0\text{A}$
Emitter Cut-Off Current	I_{EB0}	-	-	-50	nA	$V_{EB} = -3\text{V}, I_C = 0\text{mA}$
DC Current Gain	$h_{FE(1)}^*$	120	-	360		$V_{CE} = -1\text{V}, I_C = -2\text{mA}$
	$h_{FE(2)}^*$	60	-	-		$V_{CE} = -1\text{V}, I_C = -50\text{mA}$
Collector to Emitter Saturation Voltage	$V_{CE(sat)}^*$	-	-	-0.4	V	$I_C = -50\text{mA}, I_B = -5\text{mA}$
Base to Emitter Saturation Voltage	$V_{BE(sat)}^*$	-	-	-0.95	V	$I_C = -50\text{mA}, I_B = -5\text{mA}$
Collector output Capacitance	C_{ob}	-	-	4.5	pF	$V_{CB} = -5\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$
Transition Frequency	f_T	250	-	-	MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$

*Pulse test : pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 1.5\%$.